

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# T C 7 M A 2 5 7 F K

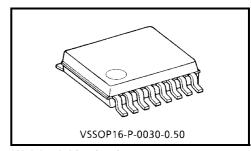
Low Voltage Quad 2-Channel Multiplexer with 3.6 V Tolerant Inputs and Outputs

The TC7MA257FK is a high performance CMOS multiplexer. Designed for use in 1.8,  $2.5\ or\ 3.3\ V$  systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to  $3.6\ V$ .

It consists of four 2-input digital multiplexers with common SELECT and  $\overline{OUTPUTENABLE}$  ( $\overline{OE}$ ).

If  $\overline{OE}$  is set high the outputs are held in a high-impedance state. The SELECT decoding determines whether the A or B inputs get routed to their corresponding Y outputs.



Weight: 0.02 g (typ.)

All inputs are equipped with protection circuits against static discharge.

#### **Features**

- Low voltage operation: VCC = 1.8~3.6 V
- High speed operation:  $t_{pd} = 3.0 \text{ ns (max) (VCC} = 3.0 \sim 3.6 \text{ V)}$

 $t_{pd} = 4.0 \text{ ns (max) (VCC} = 2.3 \sim 2.7 \text{ V})$ 

 $t_{pd} = 8.0 \text{ ns (max) (VCC} = 1.8 \text{ V)}$ 

- 3.6 V tolerant inputs and outputs.
- Output current:  $I_{OH}/I_{OL} = \pm 24 \text{ mA (min) (V}_{CC} = 3.0 \text{ V)}$

 $I_{OH}/I_{OL} = \pm 18 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$ 

 $IOH/IOL = \pm 6 \text{ mA (min) (VCC} = 1.8 \text{ V)}$ 

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

Human body model  $> \pm 2000 \text{ V}$ 

- Package: VSSOP (US16)
- · Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (\*)
  - \*: To ensure the high-impedance state during power up or power down,  $\overline{\text{OE}}$  should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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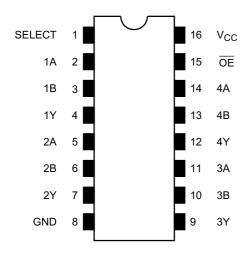
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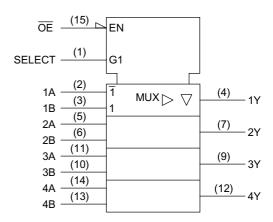
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# Pin Assignment (top view)



#### **IEC Logic Symbol**



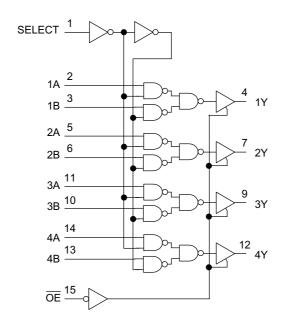
#### **Truth Table**

_				ı			
	Inputs						
ŌĒ	SELECT	Α	В	Υ			
Н	Х	Х	Х	Z			
L	L	L	Х	L			
L	L	Н	X	Н			
L	Н	X	L	L			
L	Н	Х	Н	Н			

X: Don't care

Z: High impedance

#### **System Diagram**





#### **Maximum Ratings**

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V <sub>CC</sub>	-0.5~4.6	V	
DC input voltage	V <sub>IN</sub>	-0.5~4.6	V	
DC output voltage	Vout	-0.5~4.6 (Note1)	· V	
DC output voltage	VOU1	-0.5~V <sub>CC</sub> + 0.5 (Note2)	<b>v</b>	
Input diode current	I <sub>IK</sub>	-50	mA	
Output diode current	lok	±50 (Note3)	mA	
DC output current	Гоит	±50	mA	
Power dissipation	PD	180	mW	
DC V <sub>CC</sub> /ground current	I <sub>CC</sub> /I <sub>GND</sub>	±100	mA	
Storage temperature	T <sub>stg</sub>	-65~150	°C	

Note1: Off-state

Note2: High or low state. IOUT absolute maximum rating must be observed.

Note3:  $V_{OUT} < GND, V_{OUT} > V_{CC}$ 

#### **Recommended Operating Range**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	1.8~3.6	V
Supply voltage	VCC.	1.2~3.6 (Note4)	V
Input voltage	V <sub>IN</sub>	-0.3~3.6	V
Output voltage	V	0~3.6 (Note5)	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub> (Note6)	V
		±24 (Note7)	
Output current	I <sub>OH</sub> /I <sub>OL</sub>	±18 (Note8)	mA
		±6 (Note9)	•
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V

Note4: Data retention only

Note5: Off-state

Note6: High or low state Note7:  $V_{CC} = 3.0 \sim 3.6 \text{ V}$ Note8:  $V_{CC} = 2.3 \sim 2.7 \text{ V}$ 

Note9:  $V_{CC} = 1.8 \text{ V}$ 

Note10:  $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$ 



#### **Electrical Characteristics**

# DC Characteristics (Ta = $-40\sim85^{\circ}$ C, 2.7 V < V<sub>CC</sub> $\leq$ 3.6 V)

Character	istics	Symbol	Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit
la accidenta	High level	V <sub>IH</sub>		_	2.7~3.6	2.0	_	V
Input voltage	Low level	V <sub>IL</sub>		_	2.7~3.6	_	0.8	V
				$I_{OH} = -100  \mu A$	2.7~3.6	V <sub>CC</sub> - 0.2		
	High level	Voh	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -12 mA	2.7	2.2	_	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	
Output voltage				I <sub>OH</sub> = -24 mA	3.0	2.2	_	V
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 100 \mu A$	2.7~3.6		0.2	
	Low level	VOI		I <sub>OL</sub> = 12 mA	2.7		0.4	
	Low level	w level VOL		I <sub>OL</sub> = 18 mA	3.0		0.4	
				I <sub>OL</sub> = 24 mA	3.0	_	0.55	
Input leakage curre	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.7~3.6		±5.0	μΑ
3-state output off-s	tate current	loz	$V_{IN} = V_{IH}$ or $V_{IL}$		2.7~3.6		±10.0	μА
3-state output off-state current		102	V <sub>OUT</sub> = 0~3.6 V		2.7 5.0		±10.0	μΛ
Power off leakage	current	I <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0		10.0	μΑ
Quiescent supply current		Icc	$V_{IN} = V_{CC}$ or GND		2.7~3.6		20.0	
Quiescent supply o		100	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7~3.6		±20.0	μΑ
Increase in I <sub>CC</sub> per	input	Δl <sub>CC</sub>	$V_{IH} = V_{CC} - 0.6 V$		2.7~3.6	_	750	

# DC Characteristics (Ta = -40~85°C, 2.3 V $\leq$ V<sub>CC</sub> $\leq$ 2.7 V)

Characte	ristics	Symbol	Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit
Innut voltage	High level	V <sub>IH</sub>		_	2.3~2.7	1.6	_	V
Input voltage	Low level	V <sub>IL</sub>		_	2.3~2.7	_	0.7	V
				I <sub>OH</sub> = -100 μA	2.3~2.7	V <sub>CC</sub> - 0.2	_	
	High level	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -6 \text{ mA}$	2.3	2.0	_	
				I <sub>OH</sub> = -12 mA	2.3	1.8	_	V
Output voltage				I <sub>OH</sub> = -18 mA	2.3	1.7	_	
		evel V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 100 μA	2.3~2.7	_	0.2	
	Low level			I <sub>OL</sub> = 12 mA	2.3	_	0.4	
				I <sub>OL</sub> = 18 mA	2.3	_	0.6	
Input leakage curr	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.3~2.7	_	±5.0	μА
3-state output off-state current		1	$V_{IN} = V_{IH}$ or $V_{IL}$		2.3~2.7		. 10.0	
		loz	V <sub>OUT</sub> = 0~3.6 V		2.3~2.1	_	±10.0	μΑ
Power off leakage	current	I <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0		10.0	μΑ
Outro and supply supply		loo	V <sub>IN</sub> = V <sub>CC</sub> or GND		2.3~2.7	_	20.0	Δ
Quiescent supply	Current	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3~2.7	_	±20.0	μА



#### DC Characteristics (Ta = $-40\sim85^{\circ}$ C, 1.8 V $\leq$ V<sub>CC</sub> < 2.3 V)

Characteris	Characteristics Symbol		Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit		
Input voltage	High level	V <sub>IH</sub>		_	1.8~2.3	0.7 × V <sub>CC</sub>		V		
Input voltage	Low level	V <sub>IL</sub>		_	1.8~2.3		0.2 × V <sub>CC</sub>	V		
	High level	V <sub>OH</sub>	Vон	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -100 μA	1.8	V <sub>CC</sub> - 0.2			
Output voltage	Output voltage			$I_{OH} = -6 \text{ mA}$	1.8	1.4	_	V		
	Low level	V <sub>OL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 100 \mu A$	1.8	_	0.2			
	LOW level			$I_{OL} = 6 \text{ mA}$	1.8		0.3			
Input leakage curre	Input leakage current		V <sub>IN</sub> = 0~3.6 V		1.8		±5.0	μΑ		
3-state output off-state current		I <sub>OZ</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = 0 \sim 3.6 \text{ V}$		2.3~2.7		±10.0	μА		
Power off leakage of	urrent	I <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μΑ
Quiescent supply co	Ouise cent cumply current		V <sub>IN</sub> = V <sub>CC</sub> or GND		1.8	_	20.0	пΔ		
Quiescent supply co	an <del>c</del> nt	Icc	V <sub>CC</sub> ≤ (V <sub>IN</sub> , V <sub>OUT</sub> ) ≤ 3.6 V		1.8	_	±20.0	μА		

# AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ $\Omega$ )

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Min	Max	Unit
Decrease time delegations	4		1.8	1.0	8.0	
Propagation delay time (A, B-Y)	t <sub>pLH</sub>	Figure 1, Figure 2	$2.5 \pm 0.2$	0.8	4.0	ns
(A, D-1)	t <sub>pHL</sub>		$3.3 \pm 0.3$	0.6	3.0	
Decreasion delections			1.8	1.0	9.6	
Propagation delay time (SELECT-Y)	t <sub>pLH</sub>	Figure 1, Figure 2	$2.5 \pm 0.2$	0.8	4.8	ns
(SELECT-T)	tpHL		$3.3 \pm 0.3$	0.6	4.0	
		Figure 1, Figure 3	1.8	1.0	9.2	ns
3-state output enable time	t <sub>pZL</sub>		$2.5 \pm 0.2$	0.8	4.6	
	t <sub>pZH</sub>		$3.3 \pm 0.3$	0.6	3.5	
			1.8	1.0	6.8	
3-state output disable time	t <sub>pLZ</sub>	Figure 1, Figure 3	$2.5 \pm 0.2$	0.8	3.8	ns
	t <sub>pHZ</sub>		$3.3 \pm 0.3$	0.6	3.5	
Output to output skew	1		1.8		0.5	
	t <sub>osLH</sub>	(Note11)	$2.5 \pm 0.2$	_	0.5	ns
	t <sub>osHL</sub>		$3.3 \pm 0.3$		0.5	

For  $C_L = 50 \ pF$ , add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.

 $(t_{\text{OSLH}} = |t_{\text{pLHm}} - t_{\text{pLHn}}|, \, t_{\text{OSHL}} = |t_{\text{pHLm}} - t_{\text{pHLn}}|)$ 



# Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition			Тур.	Unit
Characteristics	Syllibol	rest Condition		V <sub>CC</sub> (V)	τyp.	Oill
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$	(Note12)	1.8	0.25	
Quiet output maximum dynamic V <sub>OL</sub>	V <sub>OLP</sub>	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$	(Note12)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note12)	3.3	8.0	
	V <sub>OLV</sub>	V <sub>IH</sub> = 1.8 V, V <sub>IL</sub> = 0 V	(Note12)	1.8	-0.25	
Quiet output minimum dynamic V <sub>OL</sub>		V <sub>IH</sub> = 2.5 V, V <sub>IL</sub> = 0 V	(Note12)	2.5	-0.6	V
		V <sub>IH</sub> = 3.3 V, V <sub>IL</sub> = 0 V	(Note12)	3.3	-0.8	
Quiet output minimum dynamic V <sub>OH</sub>	V <sub>OHV</sub>	V <sub>IH</sub> = 1.8 V, V <sub>IL</sub> = 0 V	(Note12)	1.8	1.5	
		V <sub>IH</sub> = 2.5 V, V <sub>IL</sub> = 0 V	(Note12)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note12)	3.3	2.2	

Note12: This parameter is guaranteed by design.

#### **Capacitive Characteristics (Ta = 25°C)**

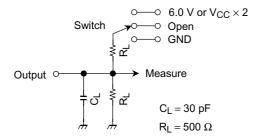
Characteristics	Symbol	Symbol Test Condition			Тур.	Unit
Gharacteristics	Symbol	rest condition		V <sub>CC</sub> (V)	τyp.	Offic
Input capacitance	C <sub>IN</sub>	_		1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C <sub>PD</sub>	$f_{IN} = 10 \text{ MHz}$	(Note13)	1.8, 2.5, 3.3	20	pF

Note13: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

#### **AC Test Circuit**



Parameter	Switch
t <sub>pLH</sub> , t <sub>pHL</sub>	Open
t <sub>pLZ</sub> , t <sub>pZL</sub>	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$
t <sub>pHZ</sub> , t <sub>pZH</sub>	GND

Figure 1



#### **AC Waveform**

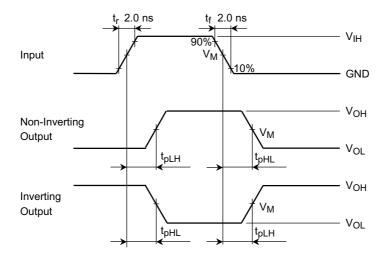


Figure 2 t<sub>pLH</sub>, t<sub>pHL</sub>

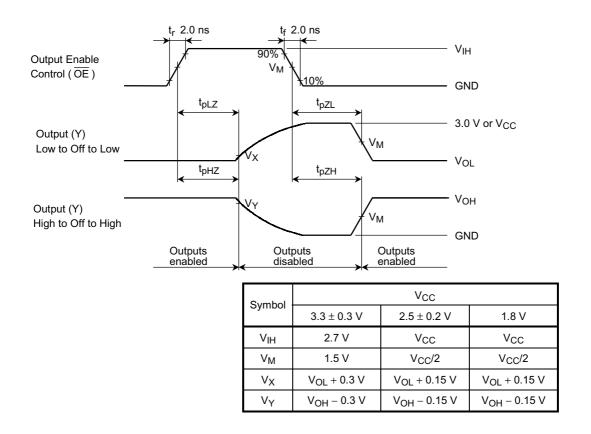
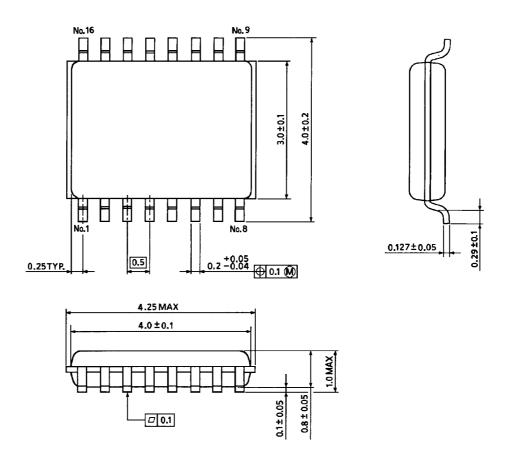


Figure 3  $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$ 

# **Package Dimensions**



Weight: 0.02 g (typ.)